



General Description

It combines advanced MOSFET technology with a low resistance package to provide extremely low

$R_{DS(ON)}$.

Features

device constructure

$R_{DS(ON)}$ to minimize conduction loss

fast switching

Application

Ordering Information:

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	80	A
	$I_{D@TC=75}$	61	A
	$I_{D@TC=100}$	50	A
Pulsed Drain Current	I_{DM}	240	A
Total Power Dissipation	$P_D@TC=25$	125	W
Total Power Dissipation	$P_D@TA=25$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	280	mJ

Fig.1 Gate-Charge Characteristics

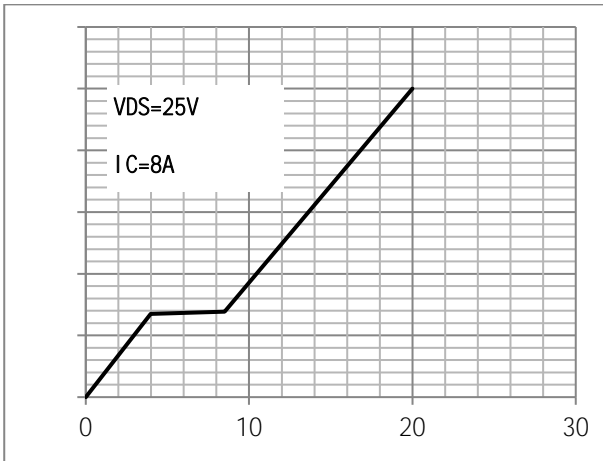


Fig.2 Capacitance Characteristics

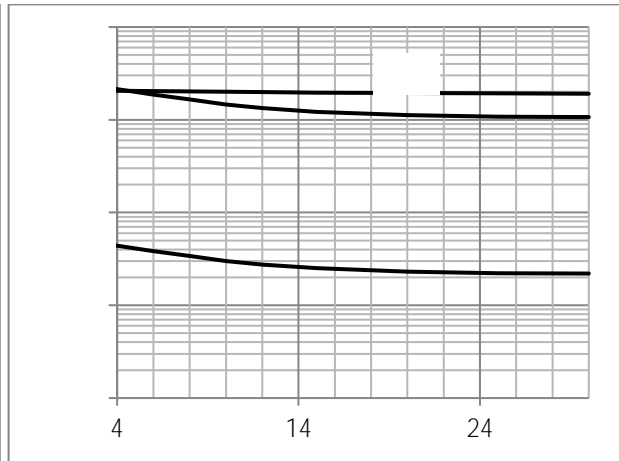


Fig.3 Power Dissipation

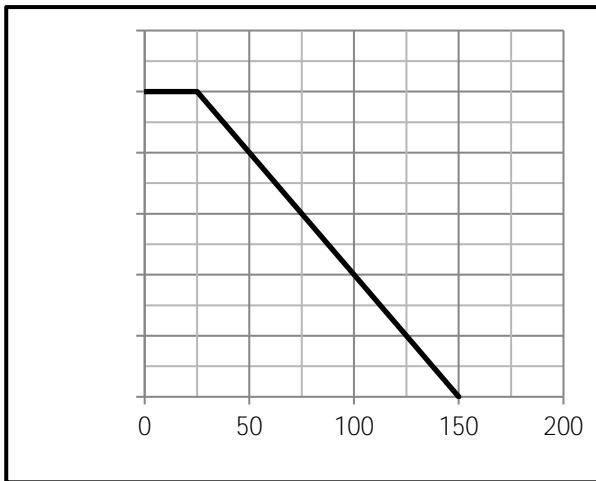


Fig.4 Typical output Characteristics

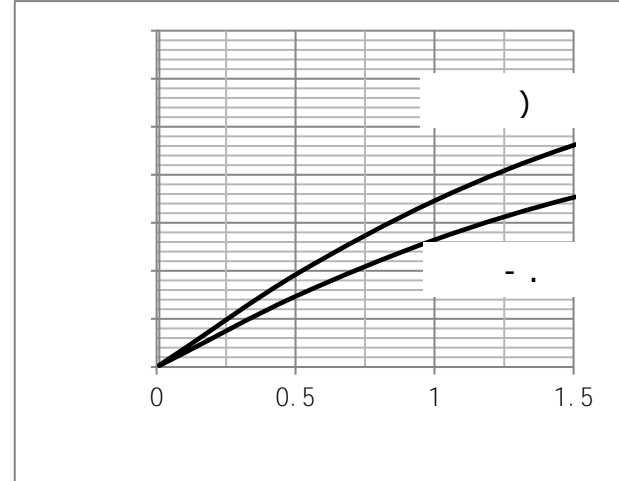


Fig.5 Threshold Voltage V.S Junction Temperature

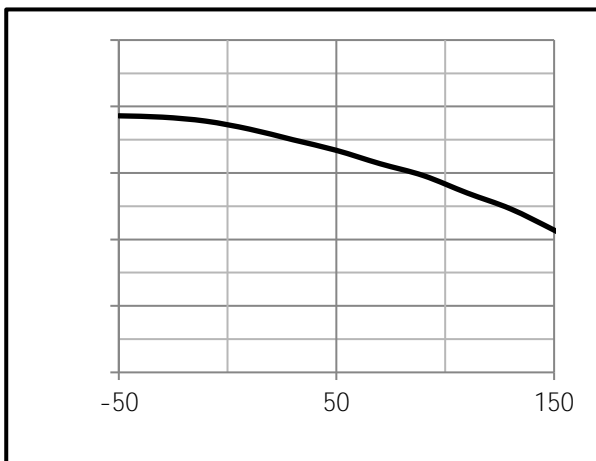
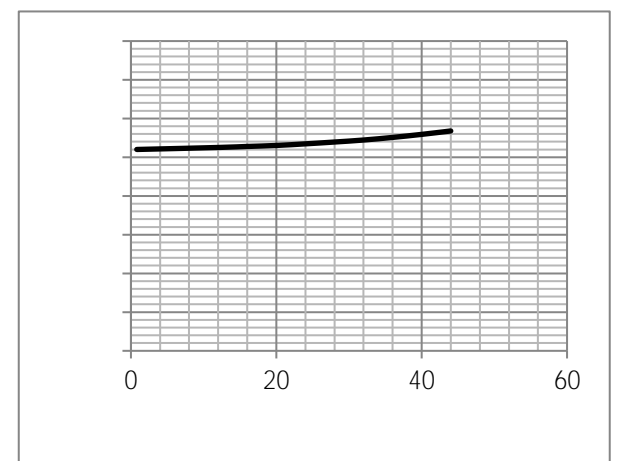


Fig.6 Resistance V.S Drain Current





0

1

Fig.9 SOA Maximum Safe Operating Area

Fig.

Fig.13 Switching Time Measurement Circuit

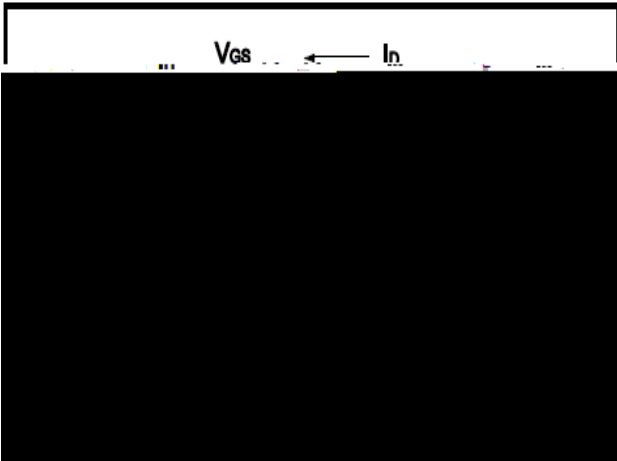
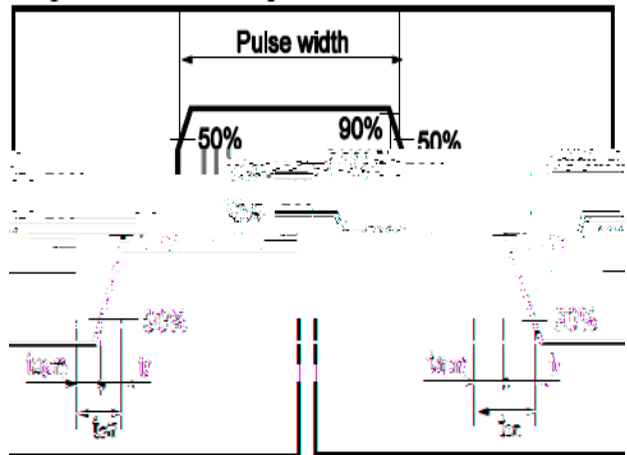


Fig.14 Gate Charge Waveform





Dimensions (TO-220)

Unit mm

	2..		2
	0.		.			0 2	
	..		2.		.		2
	.		..		0 .		2 .
	. 1		.		1..	1 .	2..
	..		.		0 .		1..
	.		.		0..		1..
					1 .		1 .

